TOSHIBA TLP166J

TOSHIBA PHOTOCOUPLER GaAs IRED + PHOTO-TRIAC

TLP166J

TRIAC DRIVE

PROGRAMMABLE CONTROLLERS

AC-OUTPUT MODULE

SOLID STATE RELAY

The TOSHIBA MINI FLAT COUPLER TLP166J is a small outline coupler, suitable for surface mount assembly.

The TLP166J consists of a photo triac, optically coupled to a gallium arsenide infrared emitting diode.

Peak Off-State Voltage: 600 V (Min.)

Trigger LED Current : 10 mA (Max.)

On-State Current : 70 mA (Max.)

Isolation Voltage : 2500 Vrms (Min.)

UL Recognized : UL1577, File No. E67349

Option (V4) type

: VDE0884 Satisfied VDE Approved

Maximum Operating Insulation Voltage: 565 Vpk Highest Permissible Over Voltage : 4000 Vpk

TRIGGER LED CURRENT

ТҮРЕ	TRIGGER LED	MARKING OF CLASSIFICATION	
(Note 1)	$V_{\rm T} = 6 \mathrm{V},$		
	Min.	Max.	CLASSIFICATION
(IFT7)	_	7	T 7
None	_	10	T7, blank

Exp. IFT7: TLP166J (IFT7)

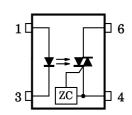
(Note 1): Application type name for certification test, please use standard product type name, i.e.

TLP166J (IFT7): TLP166J

Unit in mm 3.6 ± 0.2 0.5MIN 7.0 ± 0.4 11-4C3 **TOSHIBA** 11-4C3

Weight: 0.09 g

PIN CONFIGURATIONS



- 1. ANODE
- 3. CATHODE
- 4. TERMINAL 1
- 6. TERMINAL 2

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- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic
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MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC			SYMBOL	RATING	UNIT	
	Forward Current			50	mA	
	Forward Current Derating (Ta ≥ 53°C)			-0.7	mA/°C	
LED	Peak Forward Current (100 µs pulse,	100 pps)	I_{FP}	1	A	
	Reverse Voltage			5	V	
	Junction Temperature			125	°C	
	Off-State Output Terminal Voltage	$V_{ m DRM}$	600	V		
- 3	On-State RMS Current	$Ta = 25^{\circ}C$	IT (RMS)	70	mA	
DETECTOR	On-State KMS Current	$Ta = 70^{\circ}C$		40		
CT	On-State Current Derating (Ta ≥ 25 °C	$\Delta I_{\mathrm{T}}/^{\circ}\mathrm{C}$	-0.67	mA/°C		
ΙΈ	Peak On-State Current (100 μ s pulse,	$I_{ ext{TP}}$	2	A		
Œ	Peak Nonrepetitive Surge Current	I_{TSM}	1.2	Α		
_	(PW = 10 ms, DC = 10%)		1.2	A		
	Junction Temperature	$T_{ m j}$	115	°C		
Storage Temperature Range			$\mathrm{T_{stg}}$	-55~125	$^{\circ}\mathrm{C}$	
Operating Temperature Range			${ m T_{opr}}$	-40~100	°C	
Lead Soldering Temperature (10 s)			T_{sol}	260	°C	
Isol	Isolation Voltage (AC, 1 min., R.H. $\leq 60\%$) (Note 2)			2500	Vrms	

(Note 2): Device considered a two terminal device: Pins 1 and 3 shorted together and 4and 6 shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{AC}	_	_	240	Vac
Forward Current	${ m I_F}$	15	20	25	mA
Peak On-State Current	I_{TP}	_	_	1	Α
Operating Temperature	$T_{ m opr}$	-25	_	85	$^{\circ}\mathrm{C}$

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
	Forward Voltage	$ m V_{f F}$	$I_{\mathrm{F}} = 10 \mathrm{mA}$	1.0	1.15	1.3	V
LED	Reverse Current	$I_{ m R}$	$V_R = 5 V$	_	_	10	μ A
	Capacitance	C_{T}	V = 0, f = 1 MHz	_	30	_	pF
TOR	Peak Off-State Current	$I_{ m DRM}$	$V_{ m DRM} = 600 m V$	_	30	1000	nA
	Peak On-State Voltage	$V_{ extbf{TM}}$	$I_{TM} = 70 \text{ mA}$	_	1.7	2.8	V
	Holding Current	${ m I_H}$	_	_	0.6	_	mA
DETECTOR	Critical Rate of Rise of Off-State Voltage	dv / dt	$V_{in} = 240 \text{ Vrms}, \text{ Ta} = 85^{\circ}\text{C}$ (Note 3)	200	500	_	V/μs
[[]	Critical Rate of Rise of Commutating Voltage	dv / dt(c)	$I_T = 15 \text{ mA}, V_{in} = 60 \text{ Vrms}$ (Note 3)	_	0.2	_	V/μs

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	I_{FT}	$V_{\mathrm{T}} = 6 \mathrm{V}$	_	_	10	mA
Inhibit Voltage	$ m V_{IH}$	$I_F = Rated I_{FT}$	_	_	50	V
Leakage in Inhibited State	$I_{ m IH}$	$I_F = Rated I_{FT}$ $V_T = Rated V_{DRM}$	_	_	600	μ A
Capacitance Input to Output	$C_{\mathbf{S}}$	$V_S = 0$, $f = 1 MHz$	_	0.8	_	pF
Isolation Resistance	$R_{\mathbf{S}}$	$V_S = 500 \text{ V}, \text{ R.H.} \leq 60\%$	1×10^{12}	10^{14}	_	Ω
	BVS	AC, 1 minute	2500	_	_	Vrms
Isolation Voltage		AC, 1 second, in oil	_	5000	_	viins
		DC, 1 minute, in oil	_	5000	_	Vdc

(Note 3) : dv/dt TEST CIRCUIT

